

Peak EMI Reducing Solution

Features

- Generates an EMI optimized clock at the output.
- Input frequency: 25MHz.
- Frequency outputs:
 - 60MHz (unmodulated)
 - 2 x 48MHz (unmodulated)
 - 66.6MHz (modulated): -1.7% down spread
- Modulation rate: 30KHz.
- Supply voltage range: $3.3V \pm 0.3V$.
- Available in 8-pin SOIC Package.
- Commercial and Industrial Temperature range.
- RoHS Compliant

Product Description

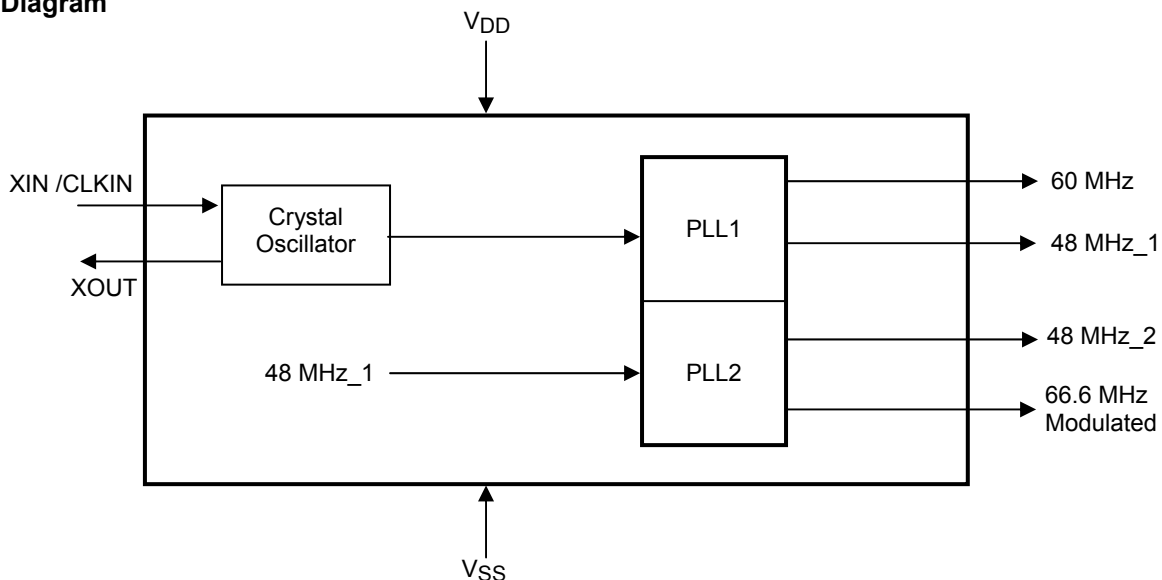
The ASM3P2111B is a versatile spread spectrum frequency modulator that reduces electromagnetic interference (EMI) at the clock source. The ASM3P2111B

allows significant system cost savings by reducing the number of circuit board layers and shielding that are required to pass EMI regulations. The ASM3P2111B modulates the output of PLL in order to spread the bandwidth of a synthesized clock, thereby decreasing the peak amplitudes of its harmonics. This results in significantly lower system EMI compared to the typical narrow band signal produced by oscillators and most clock generators. Lowering EMI by increasing a signal's bandwidth is called spread spectrum clock generation.

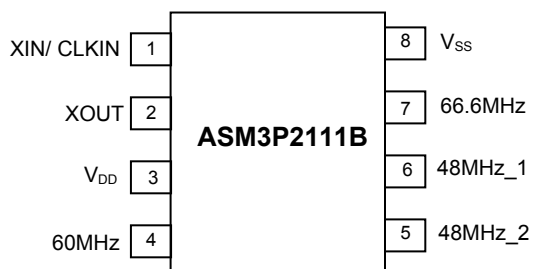
Applications

ASM3P2111B is targeted towards EMI management for high speed digital applications such as PC peripheral devices, consumer electronics and embedded controller systems.

Block Diagram



Pin Configuration



Pin Description

Pin #	Pin Name	Type	Description
1	XIN / CLKIN	I	Connection to crystal
2	XOUT	O	Connection to crystal
3	V _{DD}	P	Power supply for the analog and digital blocks (+3.3V)
4	60MHz	O	Clock output-1 60MHz un-modulated
5	48MHz_2	O	Clock output-2 48MHz_2 un-modulated
6	48MHz_1	O	Clock output-3 48MHz_1 un-modulated
7	66.6MHz	O	Clock output-4 66.6MHz modulated
8	V _{SS}	P	Ground to entire chip. Connect to System Ground

Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
V _{DD} , V _{IN}	Voltage on any pin with respect to Ground	-0.5 to +4.6	V
T _{STG}	Storage temperature	-65 to +125	°C
T _A	Operating temperature	-40 to +85	°C
T _s	Max. Soldering Temperature (10 sec)	260	°C
T _J	Junction Temperature	150	°C
T _{DV}	Static Discharge Voltage (As per JEDEC STD22- A114-B)	2	KV
Note: These are stress ratings only and are not implied for functional use. Exposure to absolute maximum ratings for prolonged periods of time may affect device reliability.			

Operating Conditions

Symbol	Parameter	Condition / Description	Min	Typ	Max	Unit
V _{DD}	Supply Voltage	3.3V ± 0.3V	3	3.3	3.6	V
F _{XIN}	Crystal Resonator Frequency		25	-	-	MHz
C _L	Output Driver Load Capacitance		-	-	15	pF

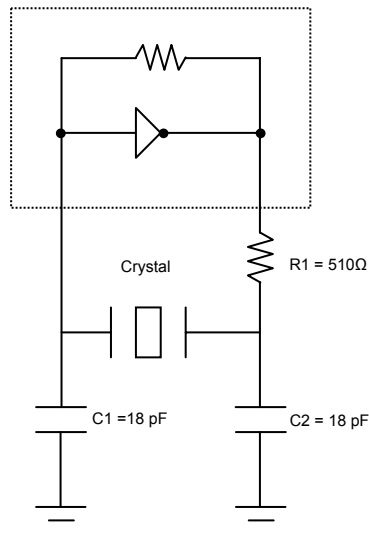
DC Electrical Characteristics

Parameter	Symbol	Conditions / Description	Min	Typ	Max	Unit
Overall						
Supply Current, Dynamic	I_{DD}	$V_{DD}=3.3V$, $F_{CLK} = 25MHz$, $C_L=15pF$	41	48	62	mA
Supply Current, Static	I_{DDL}	$V_{DD} = 3.3V$, Clock Input = 0	20	25	35	mA
All input pins						
High-Level Input Voltage	V_{IH}	$V_{DD}=3.3V$	2.0	-	$V_{DD}+0.3$	V
Low-Level Input Voltage	V_{IL}	$V_{DD}=3.3V$	$V_{SS}-0.3$	-	0.8	V
High-Level Input Current	I_{IH}		-1	-	1	μA
Low-Level Input Current (pull-up)	I_{IL}		-20	-36	-80	μA
High-Level Output Source Current	I_{xOH}	$V_{DD}=V(XIN) = 3.3V$, $V_O=0.4V$	-	3	-	mA
Low-Level Output Sink Current	I_{xOL}	$V_{DD}=3.3V$, $V(XIN)=V_O=2.5V$	-	3	-	mA
Clock Outputs						
High-Level Output Source Current	I_{OH}	$V_O=2.5V$	-	-20	-	mA
Low-Level Output Sink Current	I_{OL}	$V_O=0.4V$	-	23	-	mA
Output Impedance	Z_{OH}	$V_O=0.5 V_{DD}$; output driving high	-	29	-	Ω
	Z_{OL}	$V_O=0.5 V_{DD}$; output driving low	-	27	-	

AC Electrical Characteristics

Parameter	Symbol	Conditions/ Description	Min	Typ	Max	Unit
Rise Time	t_r	$V_O = 0.8V$ to $2.0V$; $C_L = 15pF$	300	800	900	pS
Fall Time	t_f	$V_O = 2.0V$ to $0.8V$; $C_L = 15pF$	360	800	900	pS
Clock Duty Cycle		Ratio of pulse width (as measured from rising edge to next falling edge at $V_{DD}/2$) to one clock period	45	-	55	%
* $C_L = 15 pF$, Input clock frequency = 25MHz						

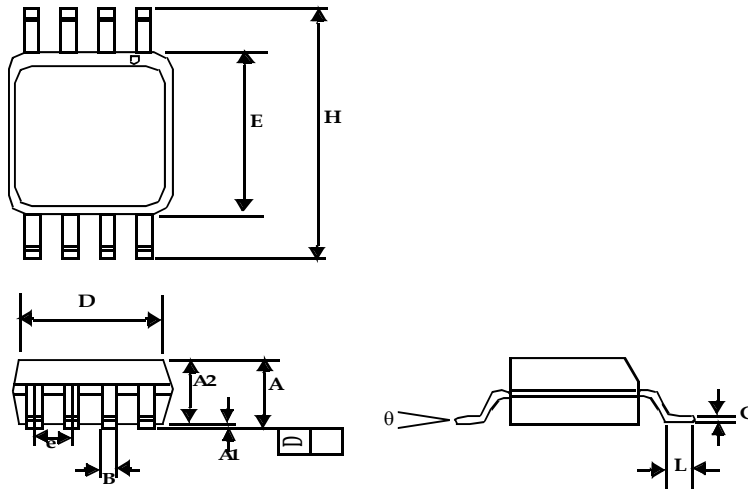
Typical Crystal Oscillator Circuit



Typical Crystal Specifications

Fundamental AT cut parallel resonant crystal	
Nominal frequency	25MHz
Frequency tolerance	± 50 ppm or better at 25°C
Operating temperature range	-25°C to +85°C
Storage temperature	-40°C to +85°C
Load capacitance	18pF
Shunt capacitance	7pF maximum
ESR	25Ω

8-lead (150-mil) SOIC Package

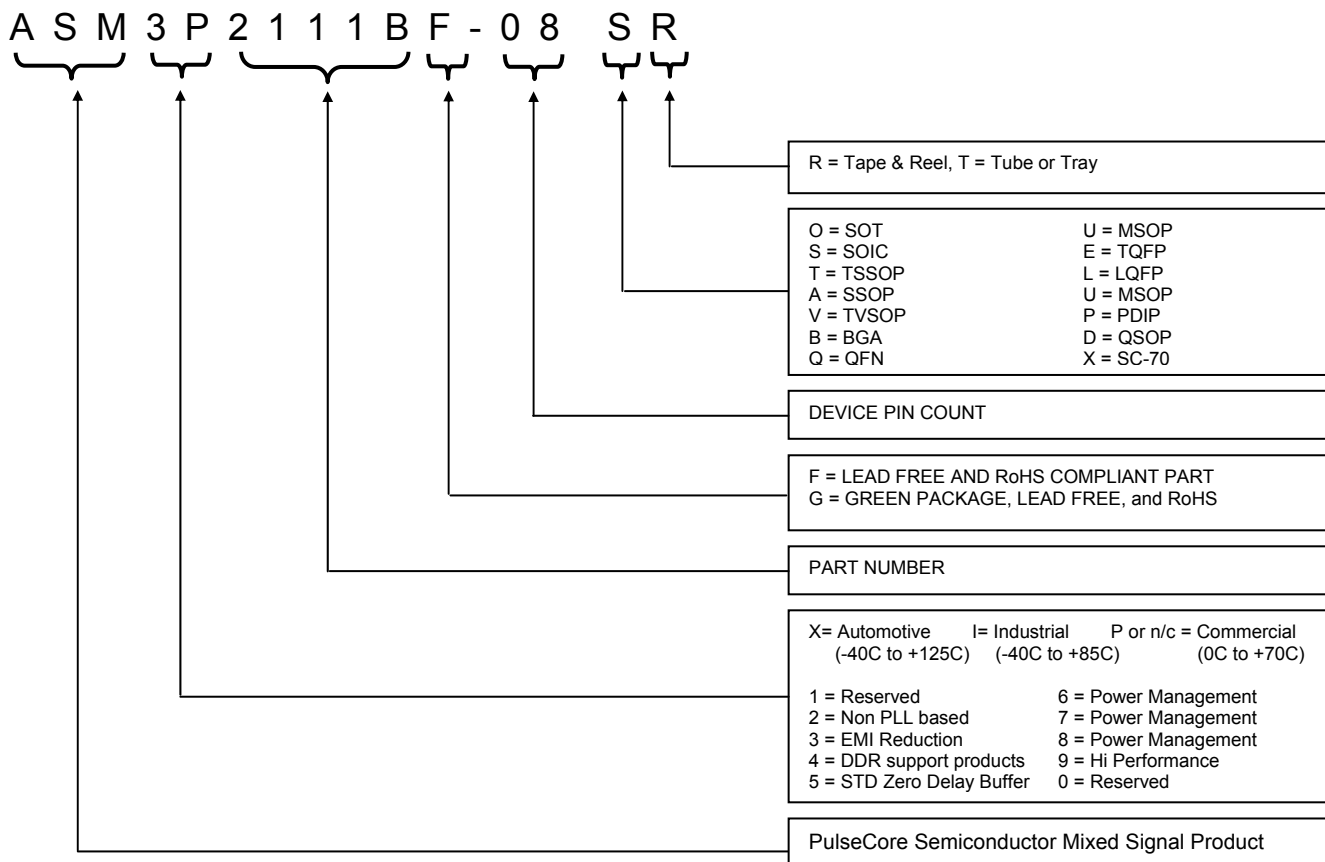


Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
A1	0.004	0.010	0.10	0.25
A	0.053	0.069	1.35	1.75
A2	0.049	0.059	1.25	1.50
B	0.012	0.020	0.31	0.51
C	0.007	0.010	0.18	0.25
D	0.193 BSC		4.90 BSC	
E	0.154 BSC		3.91 BSC	
e	0.050 BSC		1.27 BSC	
H	0.236 BSC		6.00 BSC	
L	0.016	0.050	0.41	1.27
theta	0°	8°	0°	8°

Ordering Codes

Part number	Marking	Package Configuration	Temperature Range
ASM3P2111BF-08ST	3P2111BF	8-pin SOIC TUBE, Pb Free	Commercial
ASM3P2111BF-08SR	3P2111BF	8-pin SOIC TAPE & REEL, Pb Free	Commercial
ASM3I2111BF-08ST	3I2111BF	8-pin SOIC TUBE, Pb Free	Industrial
ASM3I2111BF-08SR	3I2111BF	8-pin SOIC TAPE & REEL, Pb Free	Industrial
ASM3P2111BG-08ST	3P2111BG	8-pin SOIC TUBE, Green	Commercial
ASM3P2111BG-08SR	3P2111BG	8-pin SOIC TAPE & REEL, Green	Commercial
ASM3I2111BG-08ST	3I2111BG	8-pin SOIC TUBE, Green	Industrial
ASM3I2111BG-08SR	3I2111BG	8-pin SOIC TAPE & REEL, Green	Industrial

Ordering Information



Licensed under US patent #5,488,627, #6,646,463 and #5,631,920.



PulseCore Semiconductor Corporation
1715 S. Bascom Ave Suite 200
Campbell, CA 95008
Tel: 408-879-9077
Fax: 408-879-9018
www.pulsecoresemi.com

Copyright © PulseCore Semiconductor
All Rights Reserved
Part Number: ASM3P2111B
Document Version: v0.2

Note: This product utilizes US Patent # 6,646,463 Impedance Emulator Patent issued to PulseCore Semiconductor, dated 11-11-2003

© Copyright 2007 PulseCore Semiconductor Corporation. All rights reserved. Our logo and name are trademarks or registered trademarks of PulseCore Semiconductor. All other brand and product names may be the trademarks of their respective companies. PulseCore reserves the right to make changes to this document and its products at any time without notice. PulseCore assumes no responsibility for any errors that may appear in this document. The data contained herein represents PulseCore's best data and/or estimates at the time of issuance. PulseCore reserves the right to change or correct this data at any time, without notice. If the product described herein is under development, significant changes to these specifications are possible. The information in this product data sheet is intended to be general descriptive information for potential customers and users, and is not intended to operate as, or provide, any guarantee or warranty to any user or customer. PulseCore does not assume any responsibility or liability arising out of the application or use of any product described herein, and disclaims any express or implied warranties related to the sale and/or use of PulseCore products including liability or warranties related to fitness for a particular purpose, merchantability, or infringement of any intellectual property rights, except as express agreed to in PulseCore's Terms and Conditions of Sale (which are available from PulseCore). All sales of PulseCore products are made exclusively according to PulseCore's Terms and Conditions of Sale. The purchase of products from PulseCore does not convey a license under any patent rights, copyrights; mask works rights, trademarks, or any other intellectual property rights of PulseCore or third parties. PulseCore does not authorize its products for use as critical components in life-supporting systems where a malfunction or failure may reasonably be expected to result in significant injury to the user, and the inclusion of PulseCore products in such life-supporting systems implies that the manufacturer assumes all risk of such use and agrees to indemnify PulseCore against all claims arising from such use.